

N-Channel RF Amplifier

This device is designed for HF/VHF mixer/amplifier and applications where Process 50 is not adequate. Sufficient gain and low noise for sensitive receivers. Sourced from Process 90.

Absolute Maximum Ratings* TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V_{DG}	Drain-Gate Voltage	25	V
V_{GS}	Gate-Source Voltage	- 25	V
I _{GF}	Forward Gate Current	10	mA
T _J ,T _{stg}	Operating and Storage Junction Temperature Range	-55 to +150	٥°

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

1) These ratings are based on a maximum junction temperature of 150 degrees C.
2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics

Symbol	Characteristic		Мах	Units
		J210-212	*MMBFJ210-212	
PD	Total Device Dissipation	350	225	mW
	Derate above 25°C	2.8	1.8	mW/°C
$R_{ ext{ heta}JC}$	Thermal Resistance, Junction to Case	125		°C/W
$R_{ ext{ hetaJA}}$	Thermal Resistance, Junction to Ambient	357	556	°C/W

TA = 25°C unless otherwise noted

*Device mounted on FR-4 PCB 1.6" X 1.6" X 0.06."

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J210/J211/J212/MMBFJ210/J211/J212, Rev A

N-Channel RF Amplifier

Symbol	Parameter	Test Conditions	Min	Max	Units
OFF CHAF	RACTERISTICS				
V _{(BR)GSS}	Gate-Source Breakdown Voltage	$I_G = 1.0 \ \mu A, \ V_{DS} = 0$	- 25		V
I _{GSS}	Gate Reverse Current	$V_{GS} = 15 V, V_{DS} = 0$		- 100	pА
V _{GS(off)}	Gate-Source Cutoff Voltage	V _{DS} = 15 V, I _D = 1.0 nA 210 211 212	-1.0 - 2.5 - 4.0	-3.0 - 4.5 - 6.0	V V V
ON CHAR	ACTERISTICS				
IDSS	Zero-Gate Voltage Drain Current*	V _{DS} = 15 V, V _{GS} = 0 210 211 212	2.0 7.0 15	15 20 40	m A m A m A
gfs	GNAL CHARACTERISTICS Common Source Forward Transconductance	$V_{DS} = 15 V, V_{GS} = 0, f = 1.0 kHz$ 210 211 212	4000 6000 7000	12,000 12,000 12,000	μmho μmho μmho
goss *Pulse Test: Puls	Common Source Output Conductance se Width ≤ 300 µS	$V_{DS} = 15 V, V_{GS} = 0, f = 1.0 \text{ kHz}$		200	
*Pulse Test: Puls	Conductance se Width ≤ 300 μS al Characteristics Parameter Interactions	Com	non Drai	200	μmhos
*PulseTest: Puls Typica 100	Conductance se Width ≤ 300 µS Al Characteristics Parameter Interactions	50 Com		200	μmho: : e
*Pulse Test: Pulse Typica 100	Conductance width ≤ 300 μ S al Characteristics Parameter Interactions g_{fs} , $I_{DSS} @ V_{DS} = 10V$, $V_{GS} = 0$ PULSED $r_{DS} @ V_{DS} = 100$ mV, $V_{GS} = 0$	50 Com		200	μmhos :e = 0V
*Pulse Test: Pulse Typica 100	$\label{eq:sewidth} \underbrace{ \text{Conductance}}_{\text{Sewidth} \leq 300\mu\text{S}} \\ \hline \textbf{al Characteristics} \\ \hline \textbf{Parameter Interactions} \\ \hline \textbf{g}_{\text{fs}}, \textbf{I}_{\text{DSS}} @ \textbf{V}_{\text{DS}} = 100, \textbf{V}_{\text{GS}} = 0 \\ \hline \textbf{V}_{\text{GS}} (\textbf{OFF}) @ \textbf{V}_{\text{DS}} = 100, \textbf{V}_{\text{GS}} = 0 \\ \hline \textbf{V}_{\text{GS}} (\textbf{OFF}) @ \textbf{V}_{\text{DS}} = 100, \textbf{V}_{\text{D}} = 1.0 \\ \hline \textbf{nA} \\ \hline$	50 Com		200	μmhos :e = 0V
*Pulse Test: Pulse Typica 100	$\label{eq:sewidth} \underbrace{ \text{Conductance} } \\ \text{Sewidth} \le 300 \mu \text{S} \\ \hline \textbf{Al Characteristics} \\ \hline \textbf{Parameter Interactions} \\ \hline \textbf{g}_{\text{fs}}, \textbf{I}_{\text{DSS}} @ \textbf{V}_{\text{DS}} = 10 \text{V}, \textbf{V}_{\text{GS}} = 0 \text{PULSED} \\ \hline \textbf{r}_{\text{DS}} @ \textbf{V}_{\text{DS}} = 100 \text{ mV}, \textbf{V}_{\text{GS}} = 0 \\ \hline \textbf{V}_{\text{GS}(\text{OFF})} @ \textbf{V}_{\text{DS}} = 10 \text{V}, \textbf{I}_{\text{D}} = 1.0 \text{ nA} \\ \hline \textbf{I}_{\text{DSS}} \\ \hline \textbf{I}_{\text{DSS}} & \hline \textbf{I}_{\text{DSS}} & \hline \textbf{I}_{\text{DSS}} \\ \hline \textbf{I}_{\text{DSS}} & \hline \textbf{I}_{\text{DSS}} \\ \hline \textbf{I}_{\text{DSS}} & \hline \textbf{I}_{\text{DSS}} & \hline \textbf{I}_{\text{DSS}} \\ \hline \textbf{I}_{\text{DSS}} & \hline \textbf{I}_{\text{DSS}} & \hline \textbf{I}_{\text{DSS}} \\ \hline \textbf{I}_{\text{DSS}} & \hline \textbf{I}_{\text{DSS}} & \hline \textbf{I}_{\text{DSS}} \\ \hline \textbf{I}_{\text{DSS}} & \hline \textbf{I}_{\text{DSS}} & \hline \textbf{I}_{\text{DSS}} \\ \hline \textbf{I}_{\text{DSS}} & \hline \textbf{I}_{\text{DSS}} & \hline \textbf{I}_{\text{DSS}} & \hline \textbf{I}_{\text{DSS}} \\ \hline \textbf{I}_{\text{DSS}} & \hline \textbf{I}_{\text{DSS}} & \hline \textbf{I}_{\text{DSS}} & \hline \textbf{I}_{\text{DSS}} \\ \hline \textbf{I}_{\text{DSS}} & \hline \textbf{I}_{\text{DSS}} & \hline \textbf{I}_{\text{DSS}} & \hline \textbf{I}_{\text{DSS}} \\ \hline \textbf{I}_{\text{DSS}} & \hline \textbf{I}_{\text{DSS}} & \hline \textbf{I}_{\text{DSS}} & \hline \textbf{I}_{\text{DSS}} \\ \hline \textbf{I}_{\text{DSS}} & \hline \textbf{I}_{\text{DSS}} & \hline \textbf{I}_{\text{DSS}} & \hline \textbf{I}_{\text{DSS}} \\ \hline \textbf$	50 Com	OFF) = -4.51	200	μmhos :e = 0V
*Pulse Test: Pulse Typica 100	$\begin{tabular}{l l l l l l l l l l l l l l l l l l l $	50 Com	OFF) = -4.51	in-Sourc	μmho: :e = 0V
*Pulse Test: Pulse Typica 100	$\frac{Conductance}{Se Width ≤ 300 \mu S}$ al Characteristics Parameter Interactions $\frac{9_{fs}, I_{DSS} @ V_{DS} = 10V, V_{GS} = 0 PULSED}{V_{GS} (0 FF) @ V_{DS} = 100 mV, V_{GS} = 0}$ $\frac{V_{GS} (0 FF) @ V_{DS} = 10V, I_{D} = 1.0 nA}{I_{DSS}}$	50 Com	OFF) = -4.5V -1 -2.0V -2.5V	in-Sourc	μmho :e = 0V
*Pulse Test: Pulse Typica 100	$\frac{Conductance}{Se Width ≤ 300 \mu S}$ al Characteristics Parameter Interactions $\frac{9_{fs}, I_{DSS} @ V_{DS} = 10V, V_{GS} = 0 PULSED}{V_{GS} (0 FF) @ V_{DS} = 100 mV, V_{GS} = 0}$ $\frac{V_{GS} (0 FF) @ V_{DS} = 10V, I_{D} = 1.0 nA}{I_{DSS}}$	50 Com	OFF) = -4.5V -1 -2.0V -2.5V	in-Sourc	μmho: :e = 0V
CURRENT (mA) *Pulse Test: Puls Typica 100 200 200 200 200 200 200 200 200 200	$\frac{Conductance}{Se Width ≤ 300 \mu S}$ al Characteristics Parameter Interactions $\frac{9_{fs}, I_{DSS} @ V_{DS} = 10V, V_{GS} = 0 PULSED}{V_{GS} (0 FF) @ V_{DS} = 100 mV, V_{GS} = 0}$ $\frac{V_{GS} (0 FF) @ V_{DS} = 10V, I_{D} = 1.0 nA}{I_{DSS}}$	1000 1000 50 T _A = 25°0 TYP V _{GS} 500 TYP V _{GS} 1000 100 100 100 100 100 100 1	OFF) = -4.5V -1 -2.0V -2.5V	in-Sourc	μmho: :e = 0V

-5.0 -10

-1.0

 $V_{GS(OFF)}$ – GATE CUTOFF VOLTAGE (V)

-0.1

0

1.0

2.0

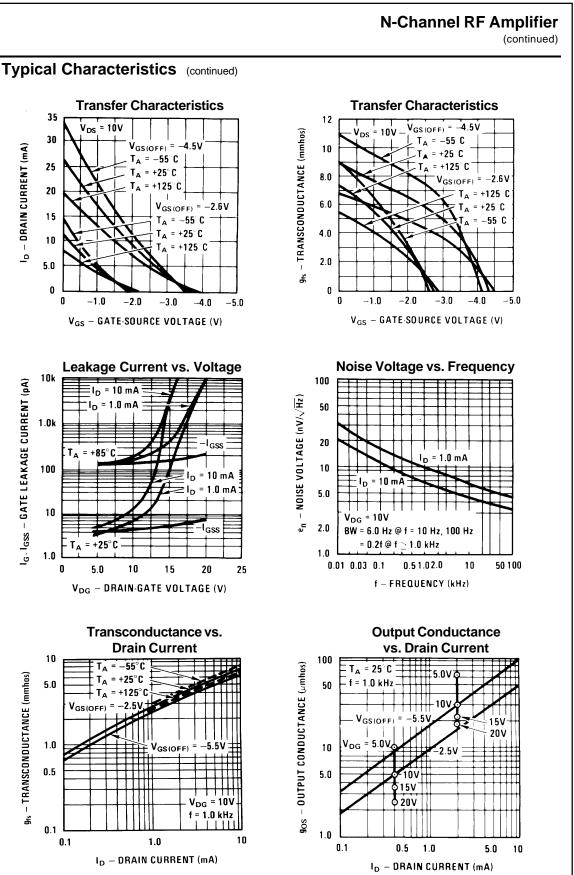
 V_{DS} – DRAIN-SOURCE VOLTAGE (V)

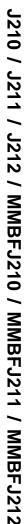
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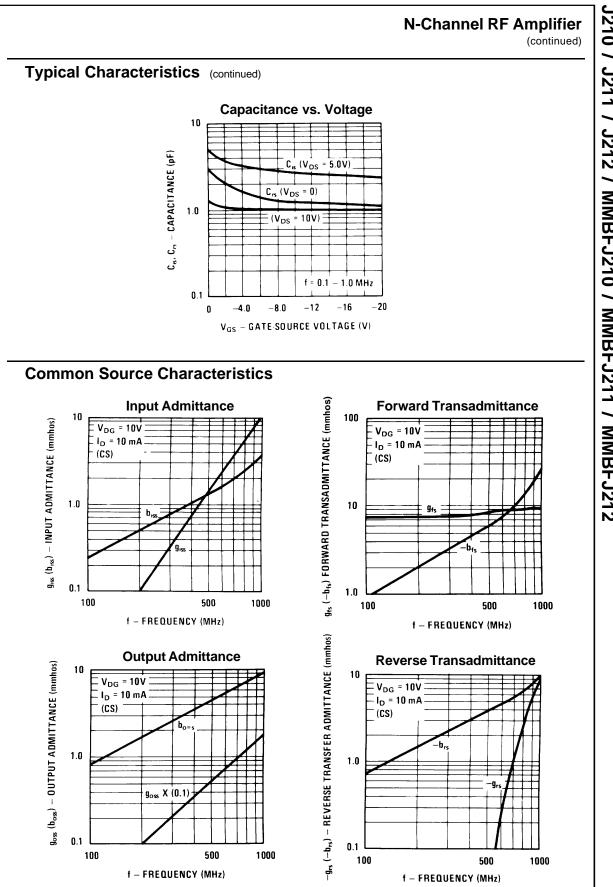
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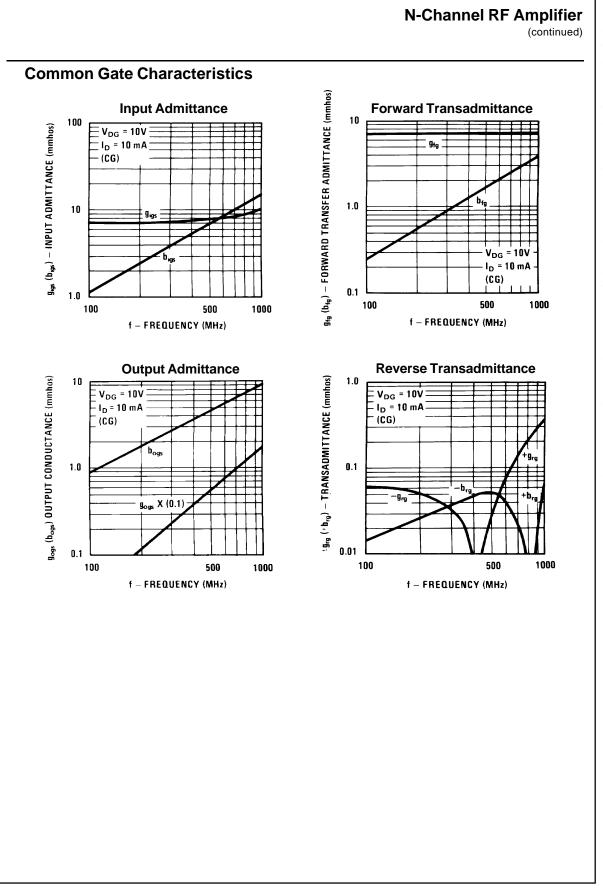
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